

## CYSJ106DFN GaAs Hall Effect Element

CYSJ106DFN series Hall-effect element is an ion-implanted magnetic field sensor made of mono-crystal gallium arsenide (GaAs) semiconductor material group III-V using ion-implanted technology. It can convert a magnetic flux density signal linearly into voltage output.

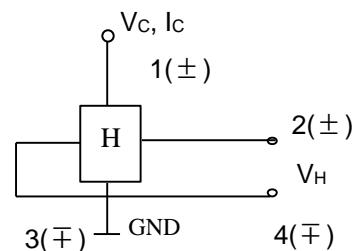
### FEATURES

- High Linearity
- Superior Temperature Stability
- Miniature Package
- Wide measuring range 0-3T

### TYPICAL APPLICATION

- Magnetic Field Measurement
- DC Brushless Motor
- Current Sensor
- Non-contact Switch
- Position Control
- Detection Of Revolution

### BLOCK DIAGRAM



### ABSOLUTE MAXIMUM RATING

Parameter	Symbol	Value	Unit
Max. Input Current/Voltage	Ic/Vc	11mA / 9.5V	mA/V
Max. Input Power	P <sub>D</sub>	105	mW
Operating temperature range	T <sub>A</sub>	-40~125	°C
Storage temperature range	T <sub>S</sub>	-40~150	°C

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C)

Parameter	Symbol	Test conditions	Value	Unit
Hall output voltage	V <sub>H</sub>	B=100mT, I <sub>c</sub> =8mA/V <sub>c</sub> =6V	110~150	mV
Offset voltage	V <sub>os</sub> (V <sub>u</sub> )	V <sub>c</sub> =6V, B=0mT	±5	mV
Input resistance	R <sub>in</sub>	B=0mT, I <sub>c</sub> =0.1mA	650~850	Ω
Output resistance	R <sub>out</sub>	B=0mT, I <sub>c</sub> =0.1mA	650~850	Ω
Temperature coefficient of Hall output voltage	αV <sub>H</sub>	I <sub>c</sub> =5mA, B=50mT (Ta=25°C ~ 125°C)	-0.06	%/°C
Temperature coefficient of input and output resistance	αR <sub>in</sub> αR <sub>out</sub>	I <sub>c</sub> =0.1mA, B=0mT (Ta=25°C ~ 125°C)	0.3	%/°C
Linearity	ΔK <sub>H</sub>	I <sub>c</sub> =5mA B=0.1/0.5T	±2	%

### Notes:

V<sub>H</sub> = V<sub>H-M</sub> - V<sub>os</sub>, where V<sub>H-M</sub> is the output voltage of Hall element, V<sub>H</sub> is the Hall voltage and V<sub>os</sub> is the offset voltage under the identical electrical stimuli.

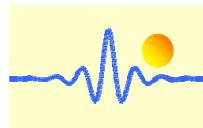
$$\alpha V_H = \frac{1}{V_H(T_1)} \times \frac{V_H(T_2) - V_H(T_1)}{T_2 - T_1} \times 100,$$

$$\Delta K_H = \frac{K(B_1) - K(B_2)}{[K(B_1) + K(B_2)]} \times 200$$

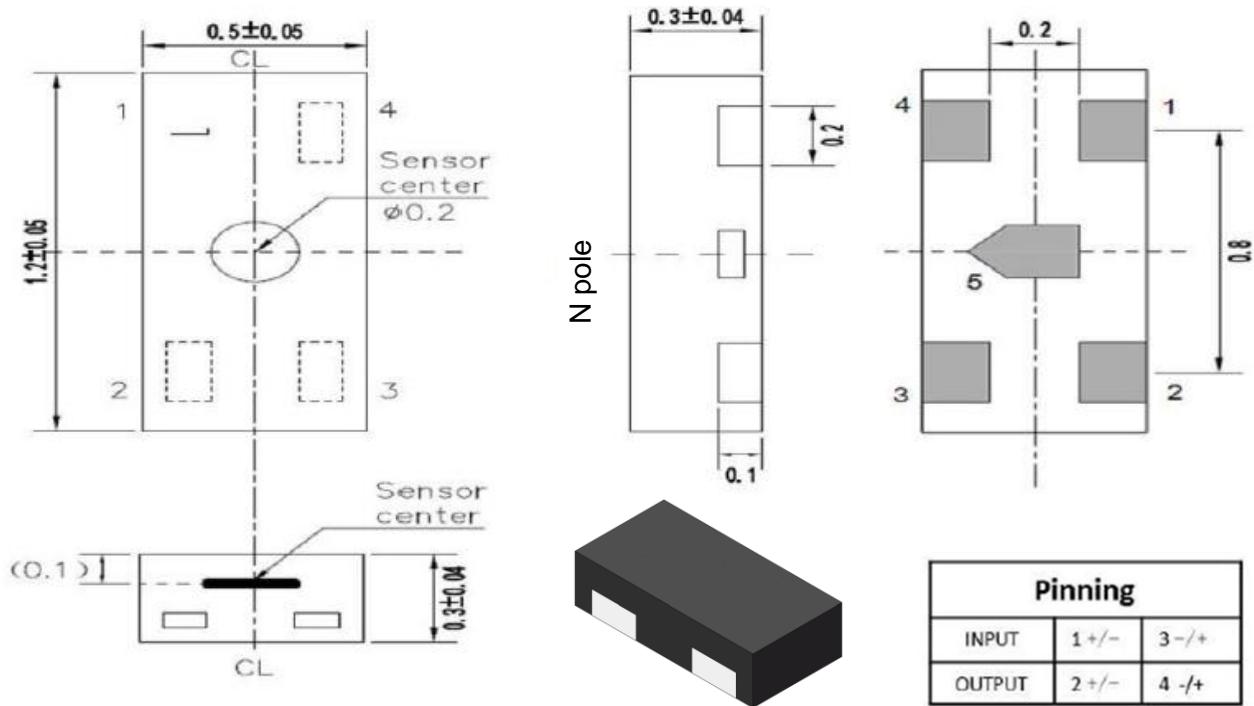
T<sub>1</sub>=25°C, T<sub>2</sub>=125°C, B<sub>1</sub>=0.5T, B<sub>2</sub>=0.1T

$$\alpha R_{in} = \frac{1}{R_{in}(T_1)} \times \frac{R_{in}(T_2) - R_{in}(T_1)}{T_2 - T_1} \times 100$$

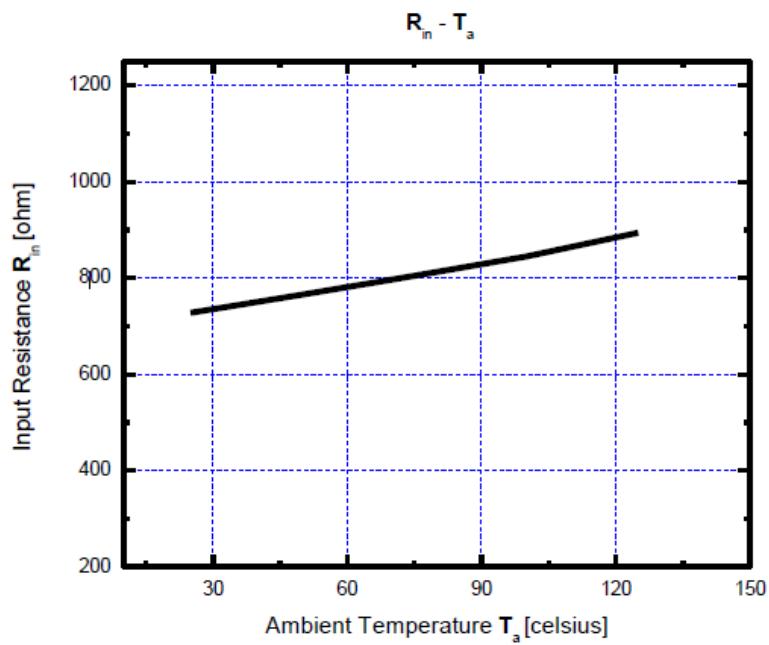
$$K_H = \frac{V_H}{I_C B}$$



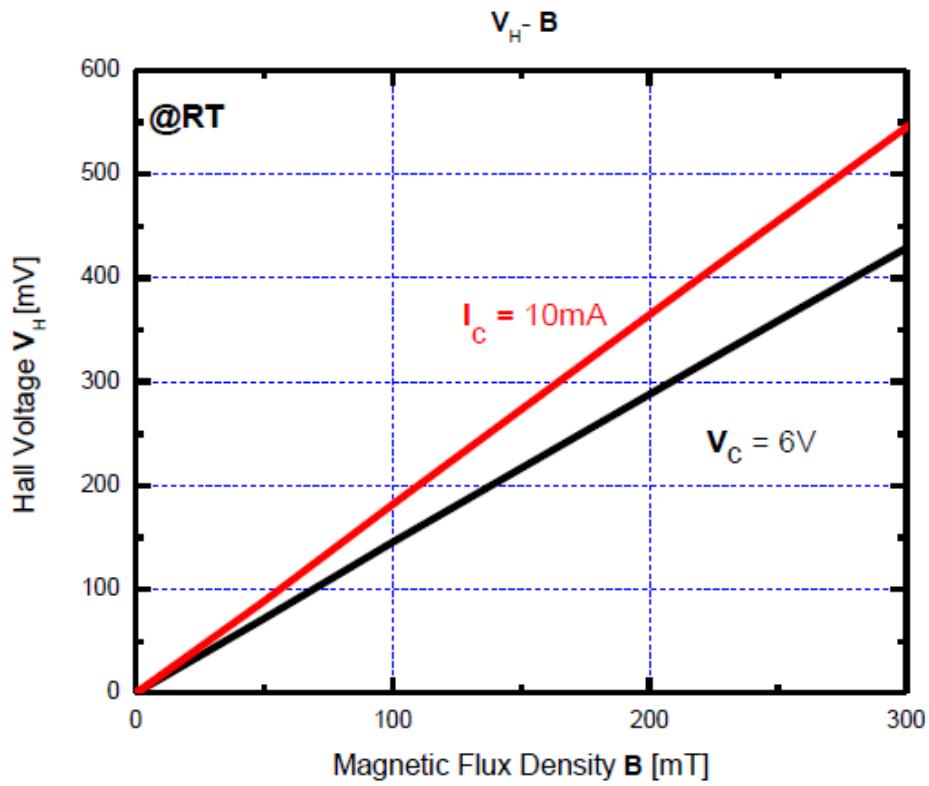
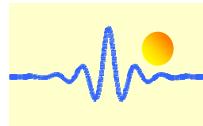
## Package Outline Drawing (Unit: mm)



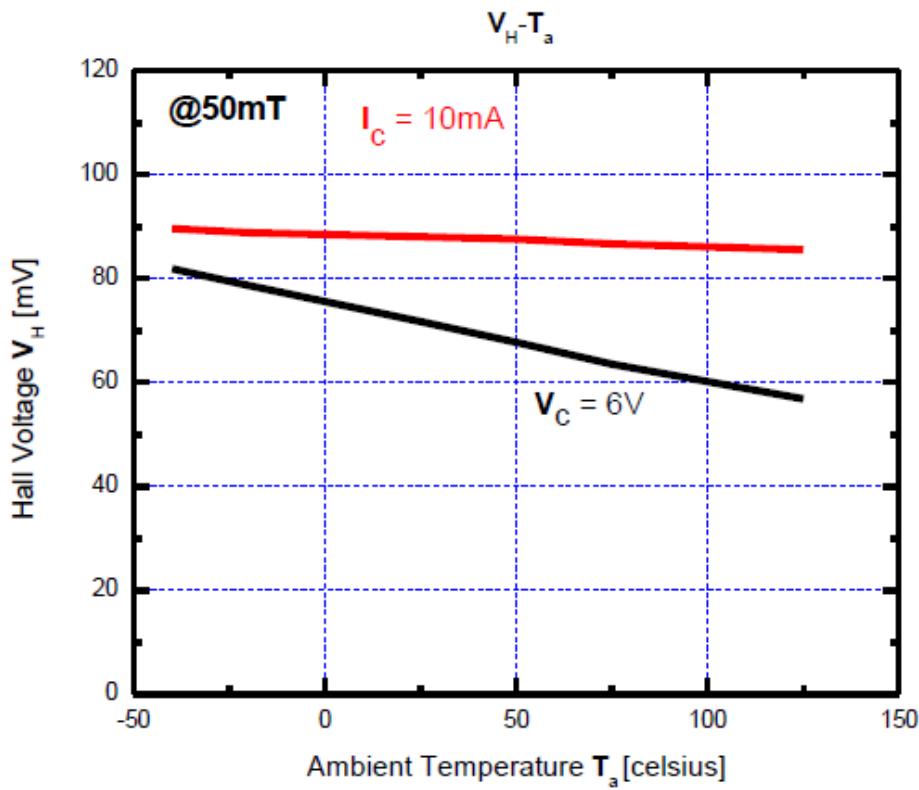
## Characteristic Curves



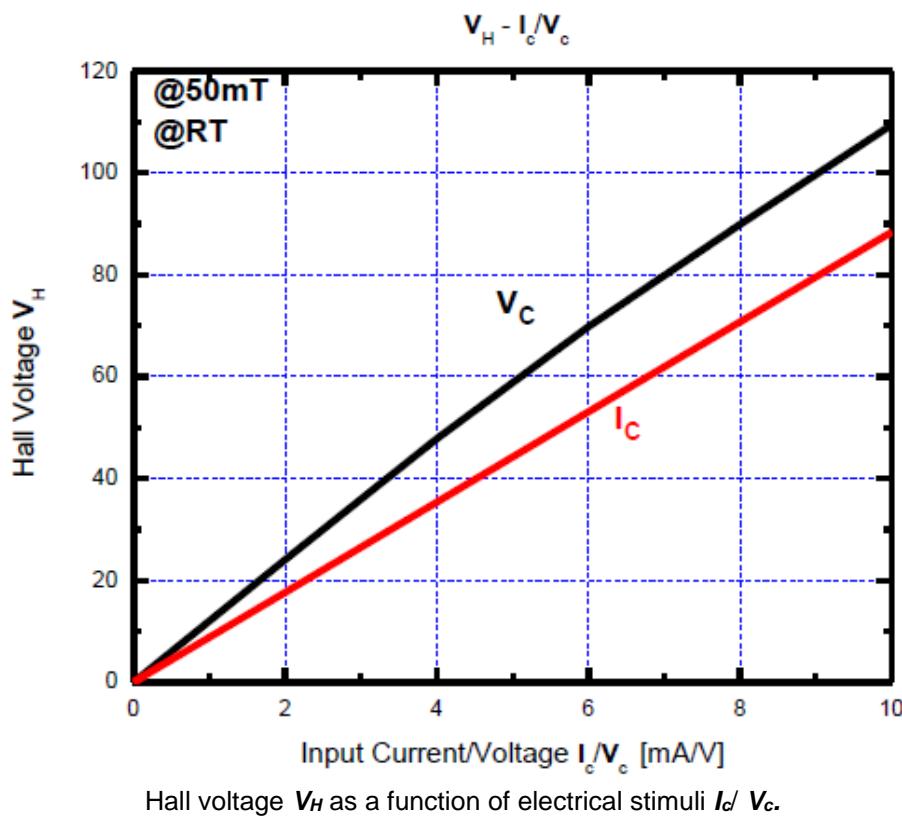
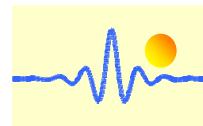
Input resistance  $R_{in}$  as a function of ambient temperature  $T_a$ .



. Hall voltage  $V_H$  as a function of magnetic flux density  $B$ .



. Hall voltage  $V_H$  as a function of ambient temperature  $T_a$ .



Hall voltage  $V_H$  as a function of electrical stimuli  $I_c/ V_c$ .

## Precautions for ESD

This product is the device that is sensitive to ESD (Electrostatic Discharge). Handling Hall Elements with the ESD-Caution mark under the environment in which

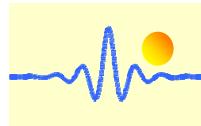
- Static electrical charge is unlikely to arise. (Ex; Relative Humidity; over 40%RH).
- Wearing the antistatic suit and wristband when handling the devices.
- Implementing measures against ESD as for containers that directly touch the devices.

## Precautions for Storage

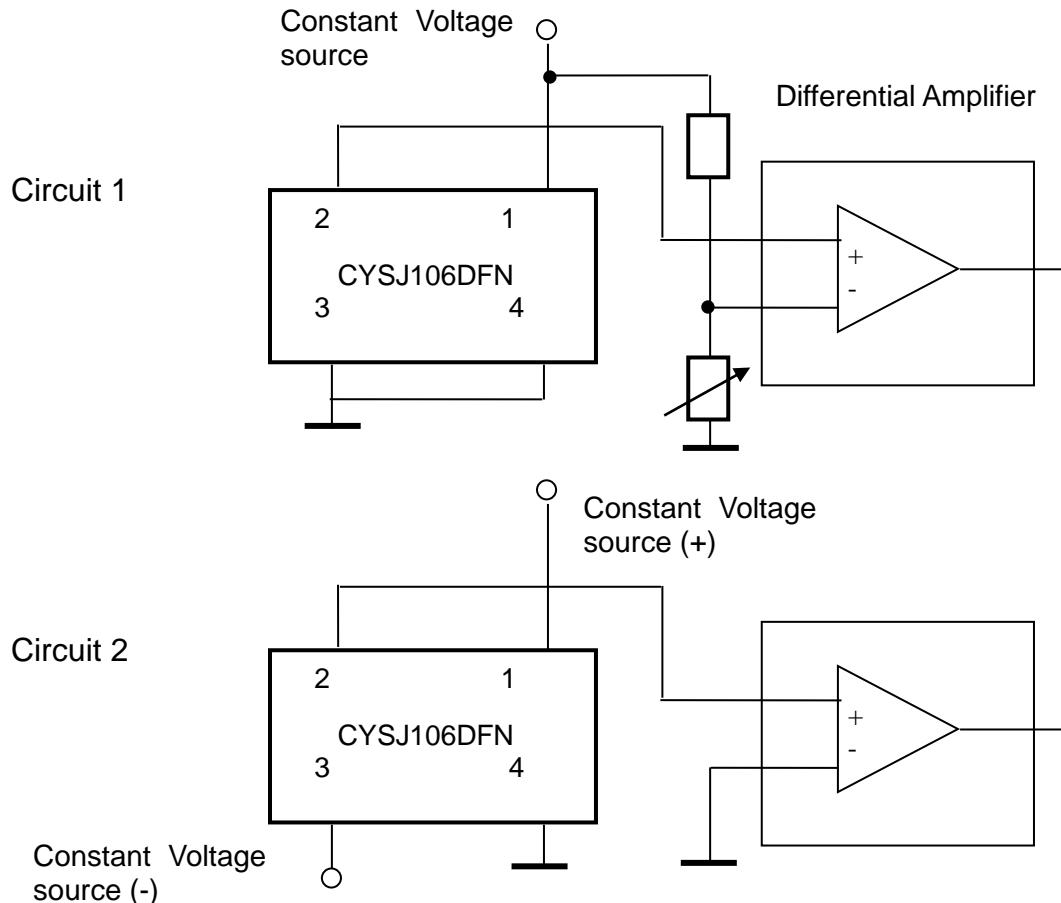
- Products should be stored at an appropriate temperature and humidity (5 to 35°C, 40 to 60%RH) after the unsealing of MBB. Keeping products away from chlorine and corrosive gas.
- Long-term storage: products are sealed in MBB.
- For storage longer than 2 years, it is recommended to store in nitrogen atmosphere with MBB sealed. Oxygen and H<sub>2</sub>O of atmosphere oxidizes leads of products and lead solder ability get worse.

## Precautions for Safety

- Do not alter the form of this product into a gas, powder or liquid through burning, crushing or chemical processing.
- Observe laws and company regulations when discarding this product.



## Connection



## Application Notes

The Hall voltage  $V_H$  can be positive and negative. But if one connects the sensor as follows (circuit 1):

- Pin 1: positive input voltage  $V_+$ , for instance +5VDC.  
Pin 3: GND  
Pin 2: OUTPUT  
Pin 4: GND

One can only measure the positive voltage at the pin 2. This means that the output voltage at zero magnetic field is not zero. This voltage is called as offset voltage. The output voltage in this case is not equal to the Hall voltage. The output voltage is equal to the sum of offset voltage and Hall voltage.

The offset voltage will be zero if you connect double power supplies  $V_+$  and  $V_-$  to the sensor (circuit 2):

- Pin 1: positive input voltage  $V_+$ , for instance +5VDC.  
Pin 3: negative input voltage  $V_-$ , for instance -5VDC  
Pin 2: OUTPUT  
Pin 4: GND

In this case the output voltage is equal to the Hall Voltage.